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Microbeam analysis — Guideline for misorientation analysis to assess mechanical damage of austenitic stainless steel by electron backscatter diffraction (EBSD)

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Contents

Page

Foreword	iv
Introduction	v
1 Scope	1
2 Normative references	1
3 Abbreviations	1
4 Terms and definitions	1
5 Equipment for EBSD measurement	4
6 Preparation	4
6.1 Calibration.....	4
6.2 Specimen preparation.....	4
7 Measurement procedures	5
7.1 Setting SEM operating conditions.....	5
7.1.1 Accelerating Voltage.....	5
7.1.2 Probe current.....	5
7.1.3 Magnification Observation.....	5
7.1.4 Working Distance.....	6
7.1.5 Focus.....	6
7.2 Setting the EBSD measurement conditions.....	6
7.2.1 Background correction.....	6
7.2.2 Binning.....	6
7.2.3 Pattern averaging.....	6
7.2.4 Hough transform.....	6
7.2.5 Measurement area.....	7
7.2.6 Step size.....	7
7.2.7 Scanning grid.....	7
8 Calculation of misorientation	7
8.1 Defining grains.....	7
8.1.1 Setting the misorientation to define grains.....	7
8.1.2 Setting of minimum grain size.....	7
8.1.3 Caution.....	8
8.2 Data screening.....	8
8.2.1 Evaluation of reliability of measured data;.....	8
8.2.2 Treatment of blank pixels.....	8
8.3 Calculation of Misorientation parameters.....	8
9 Material damage assessment	10
9.1 General.....	10
9.2 Misorientation parameter for qualitative assessments.....	10
9.3 Misorientation parameter for quantitative assessments.....	11
10 Record	11
Annex A Round robin crystal orientation measurement for damage assessment	14
Bibliography	24

Foreword

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Introduction

Mechanical damage such as creep or fatigue, in engineering materials can be assessed by misorientation analysis using electron backscatter diffraction (EBSD) technique. The EBSD technique measures crystal orientation of sample surface by indexing EBSD patterns which are acquired by scanning its surface with electron beam in a scanning electron microscope (SEM). It can give orientation maps and misorientation maps. To determine the degree of damage induced in the materials, the misorientations calculated from the mapping data are qualified by various parameters such as the local misorientation, which is an averaged misorientation between neighbouring measurement points, and intra-grain misorientations, which is an averaged misorientation between the reference orientation assigned to each crystal grain and measurement points inside the grain. These misorientation parameters correlate well with the degree of mechanical damage caused by deformation, fatigue and/or creep. Therefore, the magnitude of the material damage can be estimated using the correlation curve which represents the relationship between the misorientation parameters and the degree of the damage (hereafter called correlation curve).

In the EBSD measurement, the crystal orientation is identified through electron beam illumination to the material surface, acquisition of the EBSD pattern by an image detector, and then crystal orientation identification by indexing of the EBSD patterns. It was shown that the accuracy of the crystal orientation measurement is about 0.1–1.0°. The misorientation parameters vary depending on SEM conditions, observation conditions, EBSD pattern acquisition conditions and crystal orientation identification conditions. Several measurement parameters are determined for calculating the misorientation parameters. In particular, the local misorientation greatly depends on the distance between the measurement points (step size). Furthermore, the accuracy of the crystal orientation measurement and the definition of the misorientation parameters may depend on the hardware and software used for the measurement and analysis. There are several vendors of commercial EBSD measurement and analysis systems. The correlation curve obtained for a certain condition using a certain measurement system is not always comparable with other master curve obtained with different conditions or systems. Therefore, it will be necessary to have a standard to measure comparable master curves to show the degree of mechanical damage by using any EBSD systems.

This International Standard describes measurement procedures and conditions and definitions of misorientation parameters independent on the measurement system in order to assess damage of austenitic stainless steel precisely.

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Microbeam analysis — Guideline for misorientation analysis to assess mechanical damage of austenitic stainless steel by electron backscatter diffraction (EBSD)

1 Scope

This document describes the guideline for misorientation analysis to assess mechanical damage such as fatigue and creep induced by plastic and/or creep deformation for metallic materials by using electron backscatter diffraction (EBSD) technique. This international standard defines misorientation parameters and specifies measurement conditions for such mechanical damage assessment. This standard is recommended to evaluate mechanical damage of austenitic stainless steel, which is widely used for various components of power plants and other facilities.

In this document, the mechanical damage means the damage which causes the fracture of structural materials due to external overload, fatigue and creep; excepting the chemical and thermal damages themselves.

2 Normative references

The following referenced documents are indispensable for the application of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

ISO 13067, *Microbeam analysis — Electron backscatter diffraction — Measurement of average grain size*

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ISO 24173, *Microbeam analysis — Guidelines for orientation measurement using electron backscatter diffraction*

3 Abbreviations

CCD	charge coupled device
CMOS	complementary metal-oxide semiconductor
EBSD	electron backscatter diffraction
EBSP	electron backscatter diffraction pattern
SEM	scanning electron microscope/microscopy
WD	working distance

4 Terms and definitions

For the purpose of this document, the following terms and definitions apply.

4.1

area averaged intra-grain misorientation

average of intra grain misorientation of all pixels in the measurement area

4.2

area averaged local misorientation

average of local misorientation of all pixels in the measurement area

4.3

blank point

non-indexed point (pixel) due to insufficient quality of the EBSD pattern

Note 1 to entry: This can occur for a variety of reasons, such as insufficient specimen surface condition, dust or contamination on the specimen surface, overlapping patterns at the grain boundary, a poor-quality pattern due to the effects of strain, or if the pattern is from an unanticipated phase.

See 3.4.2 of ISO13067:2011 for definition of non-indexing.

4.4

electron backscatter diffraction (EBSD)

diffraction process that arises between the backscattered electrons and the crystal planes in a highly tilted crystalline specimen when illuminated by a stationary incident electron beam

[SOURCE: ISO24173:2009, 3.7]

4.5

electron backscatter diffraction pattern (EBSD pattern)

Kikuchi pattern like electron diffraction pattern which is generated on a phosphor screen or photographic film by backscatter diffracted electrons in a SEMA specimen is generally tilted to 70 degrees to get better quality of the diffraction pattern.

[SOURCE: ISO24173:2009, 3.8]

4.6

grain averaged intra-grain misorientation

one value for each grain by averaging intra grain misorientations

4.7

grain averaged local misorientation

average of local misorientation of all pixels in a grain

4.8

grain boundary

lines between grains in an EBSD orientation map

Grains are defined by grouping connected neighbour pixels which misorientation is less than the specified tolerance angle.

[SOURCE: ISO13067:2011, 3.2.1]

4.9

Hough transform

mathematical transformation of image processing techniques, which converts a line in an image to a point. This allows automated detection of bands in an EBSD pattern.

Note 1 to entry: In EBSD, a linear Hough transform is used to identify the position and orientation of the Kikuchi bands in each EBSD pattern, which enables the EBSD pattern to be indexed. Each Kikuchi band is identified as a bright spot in Hough space. The Hough transform is essentially a special case of the Radon transform. Generally, the Hough transform is for binary images, and the Radon transform is for grey-level images.

[SOURCE: ISO24173:2009, 3.12]

4.10

indexing reliability

numerical value that indicates the confidence/reliability of indexing result which indexing software place in automatic analysis procedure

Note 1 to entry: This parameter varies between EBSD manufacturers, but can include:

- a) the average difference between the experimentally determined angles between diffracting planes and those angles calculated for the orientation determined by EBSD software;

- b) the difference between the number of triplets (intersections of three Kikuchi bands) in the EBSD pattern matched by the chosen orientation and the next best possible solution, divided by the total number of triplets.

4.11

intra-grain misorientation

misorientation of each pixel with the average orientation of the grain (see Figure 8.2) A map that displays the deviation of a pixel to a reference orientation

4.12

local misorientation

average misorientation between the measured pixel (P1) and neighbouring pixels (see Figure 8.1) When the misorientation between the measured pixel (P2) and neighbour pixel exceeds the threshold angle like the measured pixels at the grain boundary as shown in [Fig. 8.1](#), these pixels are excluded from the misorientation calculation.

4.13

master curve

correlation curve obtained experimentally between misorientation parameter and mechanical damage degree It is used to estimate damage degree quantitatively.

4.14

minimum grain size

Once the grain grouping algorithm has completed, if the sum number of measurements constituting a grain are less than this value then the grain is excluded.

4.15

misorientation

given two crystal orientations, the misorientation is the rotation, often defined by an angle/axis pair, required to rotate one set of crystal axes into coincidence with the other set of crystal axes. The smallest angle used here.

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4.16

misorientation parameter

general term indicates parameter calculated from misorientation such as “local misorientation”, “intra-grain misorientation” It is classified as 3 groups; parameter for each pixel, grain or area.

4.17

pattern quality

measure of the sharpness of the diffraction bands or the range of contrast within a diffraction pattern

Note 1 to entry: Different terms are used in different commercial software packages, including, for example, band contrast, band slope and image quality.

4.18

pixel

Smallest area of an EBSD map, with the dimensions of the step size, to which is assigned the result of a single orientation measurement made by stopping the beam at a point at the center of that area

[SOURCE: ISO13067:2011, 3.1.2]

Note 1 to entry: This is different from ‘camera pixels’.

4.19

scanning grid

A regular hexagonal grid or a regular square grid is adopted generally. A hexagonal (square) grid means the individual points making up the scan area a situated on a hexagonal (or square) array.

4.20

step size

distance between adjacent points from which individual EBSD patterns are acquired during collection of data for an EBSD map

[SOURCE: ISO13067:2011, 3.1.1]

5 Equipment for EBSD measurement

See 4 of ISO24173:2009.

5.1 SEM, EPMA or FIB instrument, fitted with an electron column and including controls for beam position, stage, focus and magnification.

5.2 Accessories, for detecting and indexing electron backscatter diffraction patterns, including:

Phosphorescent (“phosphor”) screen, which is fluoresced by electrons from the specimen to form the diffraction pattern.

Image acquisition device, with low light sensitivity, for viewing the diffraction pattern produced on the screen.

Computer, with image processing, computer-aided pattern indexing, data storage and data processing, and SEM beam (or stage) control to allow mapping.

NOTE 1 Modern systems generally use charge-coupled devices (CCDs) or complementary metal-oxide semiconductor (CMOS).

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6 Preparation

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6.1 Calibration

The procedures described in ISO 24173 shall be followed.

6.2 Specimen preparation

The areas chosen for examination shall be representative of location of interest, and, if there is variation with position in the specimen, the positions examined shall be recorded in relation to the specimen geometry.

The procedures set out in Annex B of ISO 24173 shall be followed.

For specimen preparation for EBSD analysis, the following equipment might be required (depending on the types of specimen to be prepared — see Annex B of ISO 24173): cutting and mounting equipment, mechanical grinding and polishing equipment, electrolytic polisher, ultrasonic cleaner, ion-sputtering equipment and coating equipment.

It is also needed to be considered to avoid any phase transformation during specimen preparation.

Undesired damage on the specimen surface must be removed carefully. In order to obtain the desired damage-free surface for misorientation analysis, final polishing using colloidal silica is effective. If scratches remain on the surface, they cause larger misorientation as shown in [Fig. 6.1](#)